

N-channel 600 V, 0.71 Ω typ., 5.5 A MDmesh™ M2 Power MOSFET in a TO-220FP package

Datasheet - production data

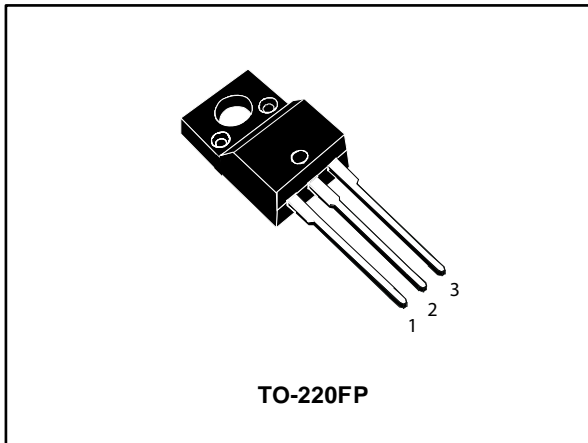
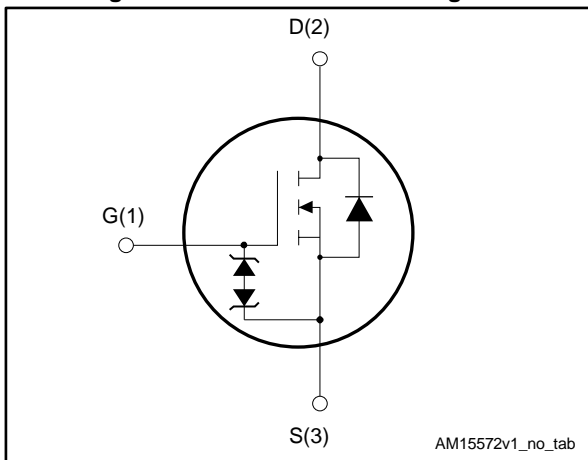


Figure 1: Internal schematic diagram



Features

Order code	V _{DS}	R _{DS(on)} max.	I _D
STF9HN65M2	600 V	0.82 Ω	5.5 A

- Extremely low gate charge
- Excellent output capacitance (C_{oss}) profile
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using MDmesh™ M2 technology. Thanks to its strip layout and an improved vertical structure, the device exhibits low on-resistance and optimized switching characteristics, rendering it suitable for the most demanding high efficiency converters.

Table 1: Device summary

Order code	Marking	Package	Packing
STF9HN65M2	9HN65M2	TO-220FP	Tube

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1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 25	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	5.5	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	3.5	A
$I_{DM}^{(2)}$	Drain current (pulsed)	22	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	20	W
$dv/dt^{(3)}$	Peak diode recovery voltage slope	15	V/ns
$dv/dt^{(4)}$	MOSFET dv/dt ruggedness	50	V/ns
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink ($t = 1\text{ s}$, $T_C = 25\text{ }^\circ\text{C}$)	2500	V_{ISO}
T_{stg}	Storage temperature	- 55 to 150	°C
T_j	Max. operating junction temperature	150	

Notes:

- (1) Limited only by maximum temperature allowed.
 (2) Pulse width limited by safe operating area.
 (3) $I_{SD} \leq 5.5\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$; $V_{DS\text{ peak}} < V_{(BR)DSS}$, $V_{DD} = 80\% V_{(BR)DSS}$.
 (4) $V_{DS} \leq 520\text{ V}$.

Table 3: Thermal data

Symbol	Parameter	Value	Unit
$R_{thj\text{-case}}$	Thermal resistance junction-case max.	6.25	°C/W
$R_{thj\text{-amb}}$	Thermal resistance junction-ambient max.	62.5	°C/W

Table 4: Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (pulse width limited by $T_{j\text{max}}$)	1.0	A
E_{AS}	Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	105	mJ

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified).

Table 5: Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$, $I_D = 1\text{ mA}$	650			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$, $V_{DS} = 650\text{ V}$			1	μA
		$V_{GS} = 0\text{ V}$, $V_{DS} = 650\text{ V}$, $T_C = 125\text{ °C}$			100	μA
I_{GSS}	Gate-body leakage current	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 25\text{ V}$			± 10	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 2.5\text{ A}$		0.71	0.82	Ω

Table 6: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0\text{ V}$	-	325	-	pF
C_{oss}	Output capacitance		-	16	-	pF
C_{rss}	Reverse transfer capacitance		-	0.85	-	pF
$C_{oss\ eq.}^{(1)}$	Equivalent output capacitance	$V_{DS} = 0\text{ V to } 520\text{ V}$, $V_{GS} = 0\text{ V}$	-	109	-	pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	5.6	-	Ω
Q_g	Total gate charge	$V_{DD} = 520\text{ V}$, $I_D = 5\text{ A}$, $V_{GS} = 10\text{ V}$ (see Figure 15: "Gate charge test circuit")	-	11.5	-	nC
Q_{gs}	Gate-source charge		-	2.5	-	nC
Q_{gd}	Gate-drain charge		-	5	-	nC

Notes:

⁽¹⁾ $C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS} .

Table 7: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 325\text{ V}$, $I_D = 2.5\text{ A}$, $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$ (see Figure 14: "Switching times test circuit for resistive load" and Figure 19: "Switching time waveform")	-	7.5	-	ns
t_r	Rise time		-	4.6	-	ns
$t_{d(off)}$	Turn-off-delay time		-	24	-	ns
t_f	Fall time		-	14.5	-	ns

Table 8: Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		5.5	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		22	A
$V_{SD}^{(2)}$	Forward on voltage	$V_{GS} = 0\text{ V}$, $I_{SD} = 5\text{ A}$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$ (see Figure 16: "Test circuit for inductive load switching and diode recovery times")	-	268		ns
Q_{rr}	Reverse recovery charge		-	1.7		μC
I_{RRM}	Reverse recovery current		-	12.5		A
t_{rr}	Reverse recovery time	$I_{SD} = 5\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$, $T_J = 150\text{ }^\circ\text{C}$ (see Figure 16: "Test circuit for inductive load switching and diode recovery times")	-	408		ns
Q_{rr}	Reverse recovery charge		-	2.6		μC
I_{RRM}	Reverse recovery current		-	13		A

Notes:

(1) Pulse width is limited by safe operating area.

(2) Pulse test: pulse duration = 300 μs , duty cycle 1.5%.

2.1 Electrical characteristics (curves)

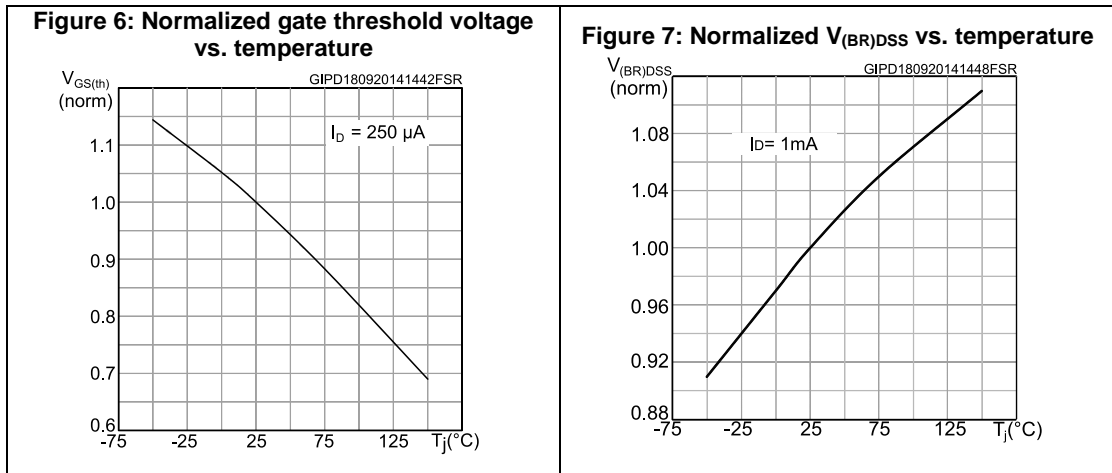
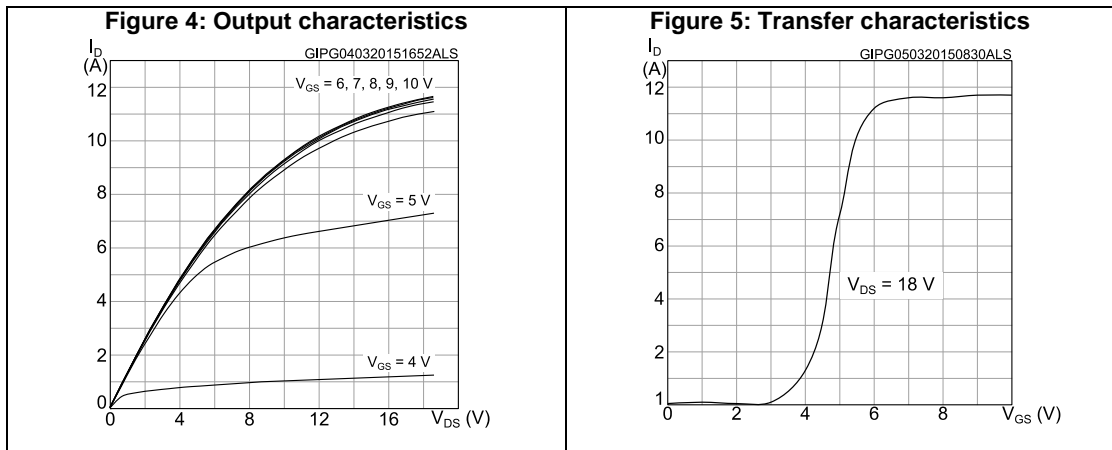
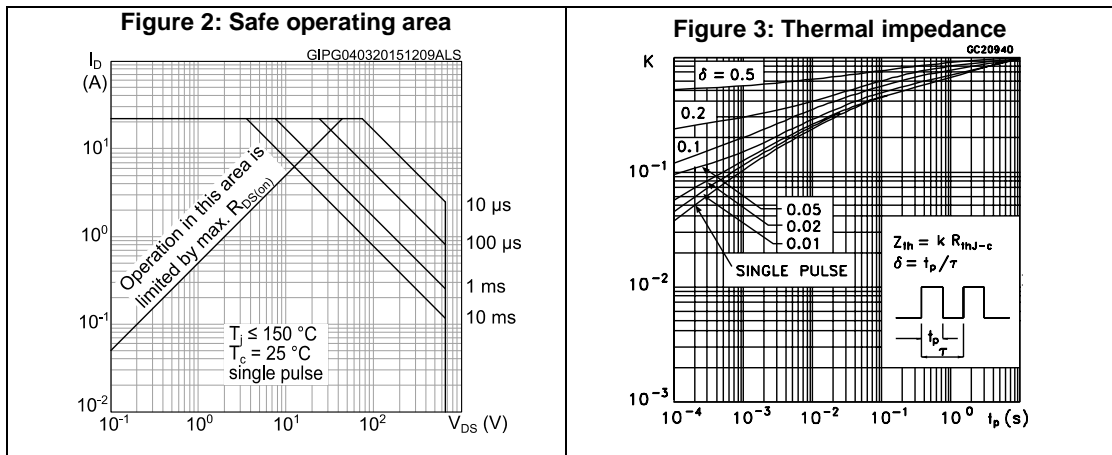


Figure 8: Static drain-source on-resistance

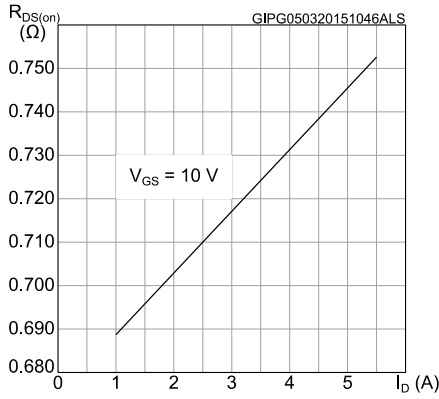


Figure 9: Normalized on-resistance vs. temperature

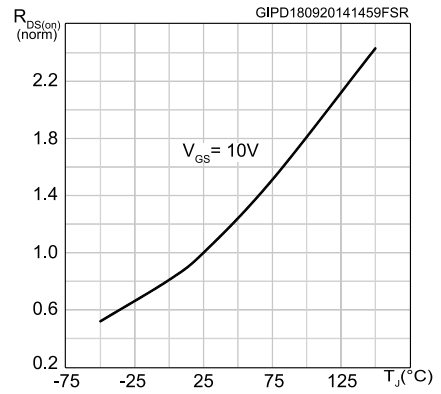


Figure 10: Gate charge vs. gate-source voltage

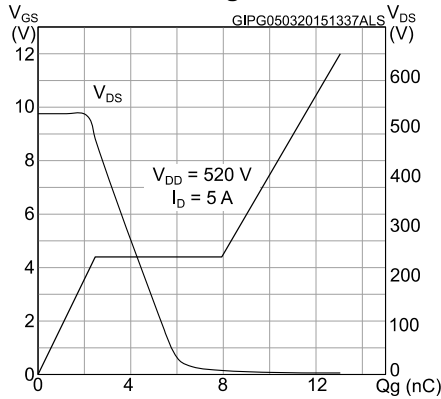


Figure 11: Capacitance variations

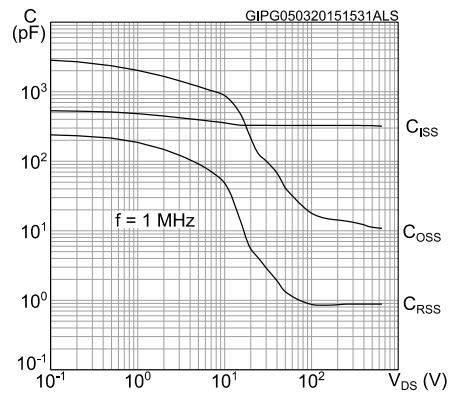


Figure 12: Output capacitance stored energy

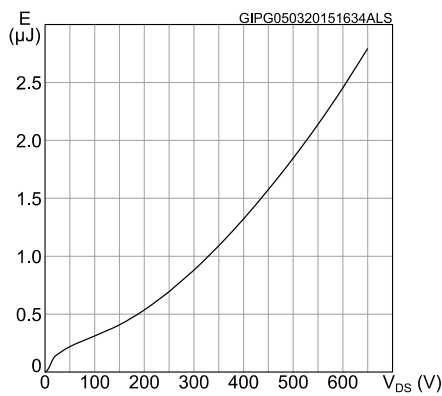
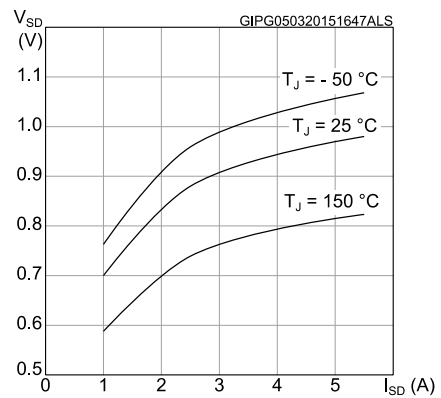
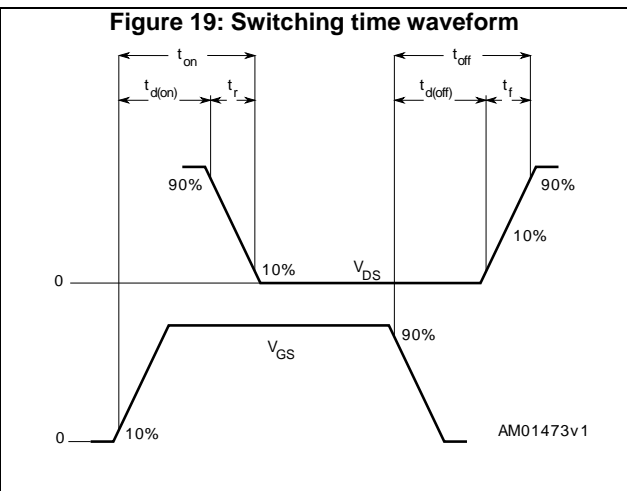
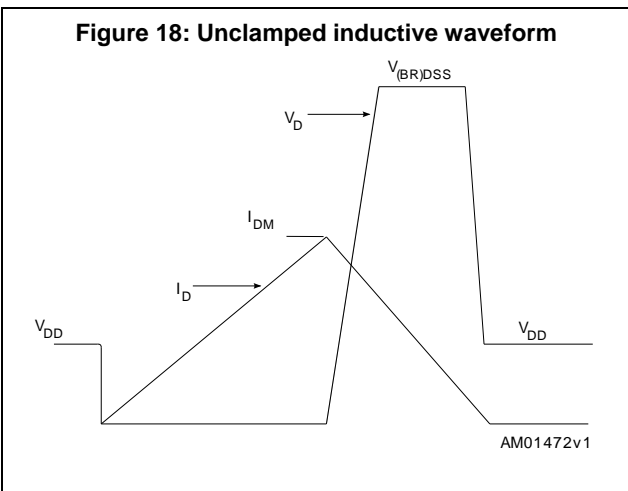
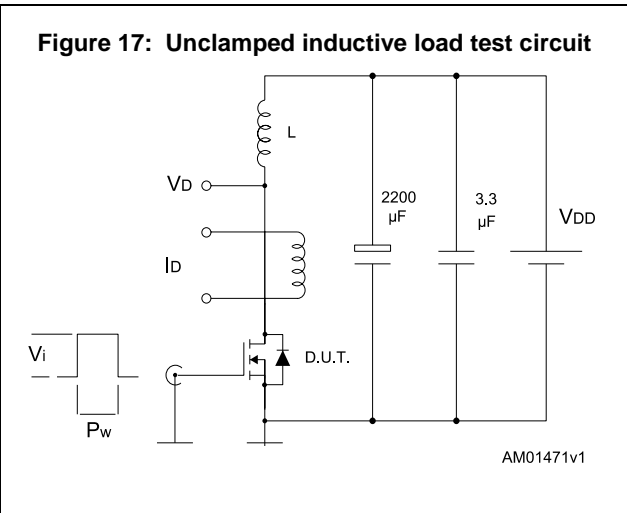
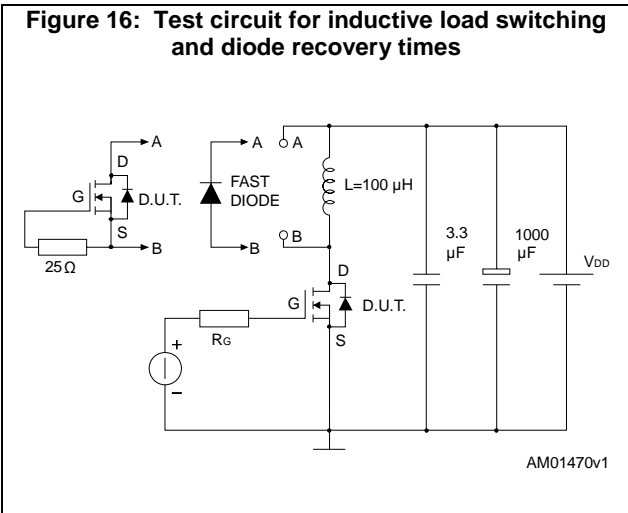
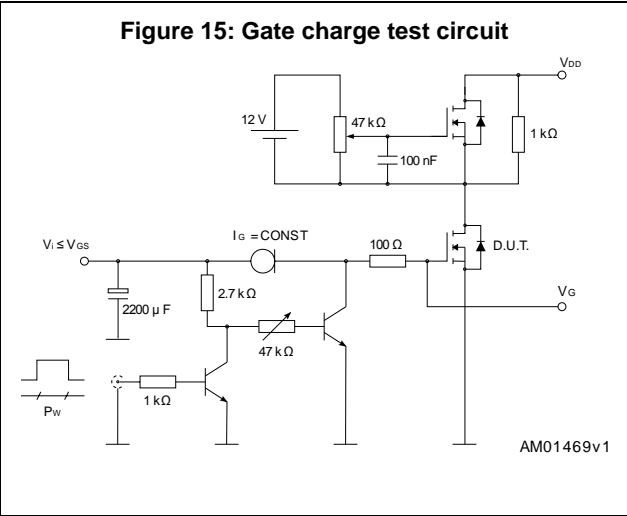
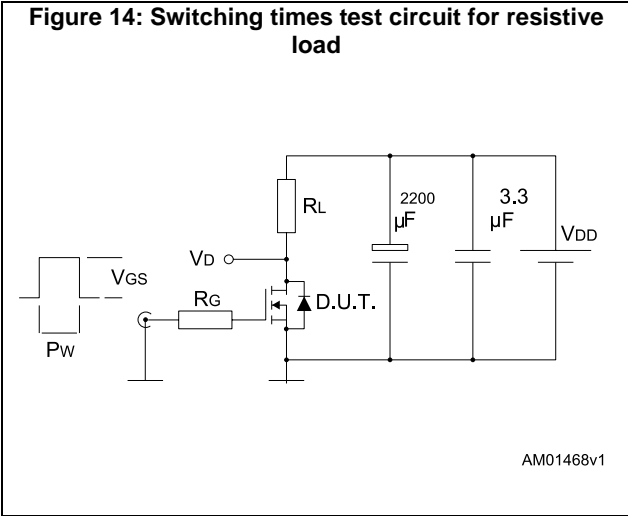


Figure 13: Source-drain diode forward characteristics



3 Test circuits

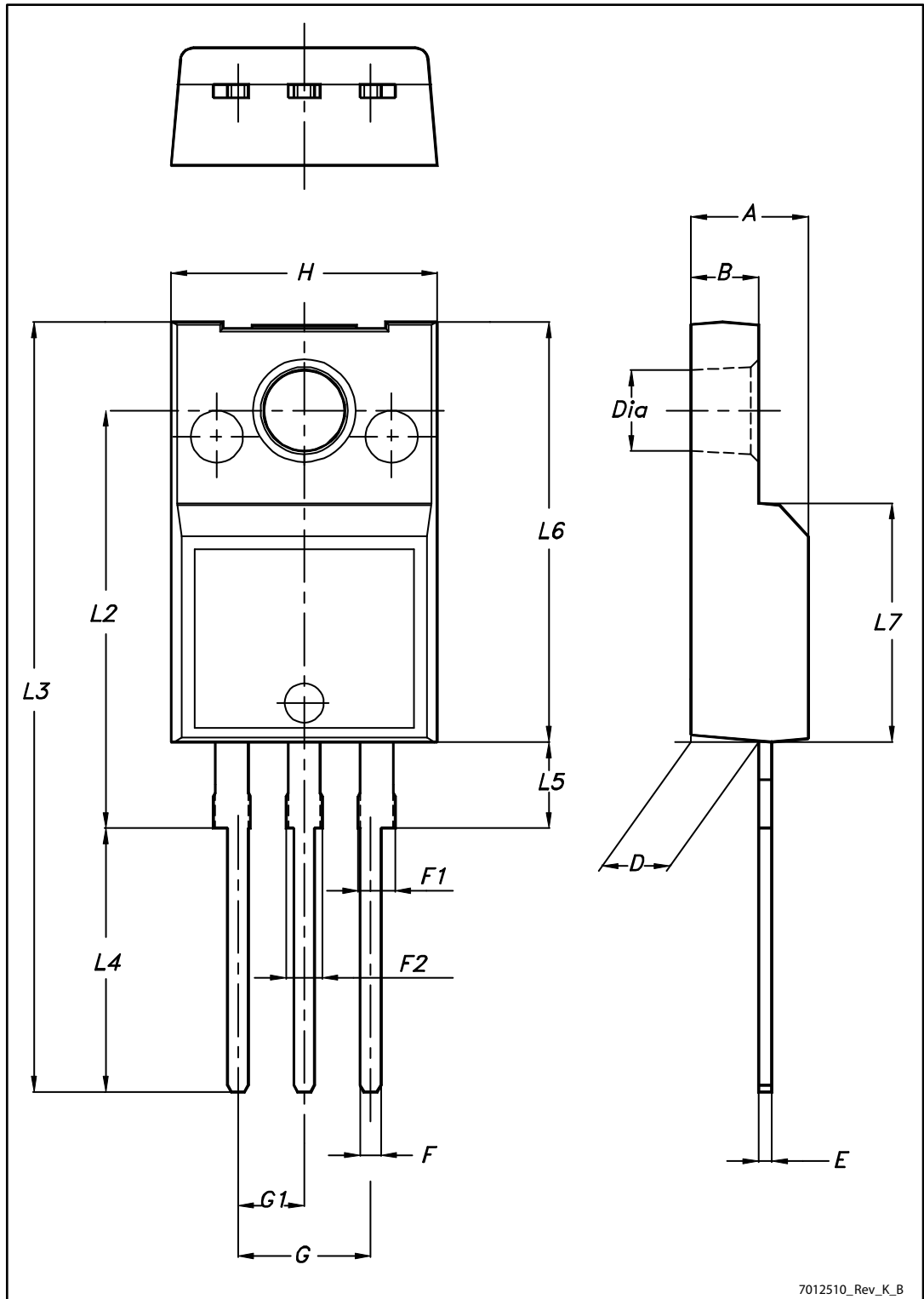


4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

4.1 TO-220FP package information

Figure 20: TO-220FP package outline



7012510_Rev_K_B

Table 9: TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

5 Revision history

Table 10: Document revision history

Date	Revision	Changes
11-Mar-2015	1	Initial release.
23-Apr-2015	2	Document status promoted to 'Production data'.

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